20A, 35V - 200V Schottky Barrier Rectifier

FEATURES

- AEC-Q101 qualified available
- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

MECHANICAL DATA

- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.88g (approximately)

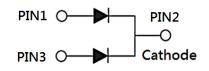
KEY PARAMETERS				
PARAMETER	VALUE	UNIT		
١ _F	20	A		
V _{RRM}	35 - 200	V		
I _{FSM}	150	А		
T _{J MAX}	150	°C		
Package	TO-220AB			
Configuration	Dual dies			







TO-220AB



		MBR	MBR	MBR	MBR	MBR	MBR	MBR	MBR	
PARAMETER	SYMBOL	2035	2045	2050	2060	2090	20100	20150	20200	UNIT
		СТ	СТ	СТ	СТ	СТ	СТ	СТ	СТ	
Marking code on the device		MBR 2035 CT	MBR 2045 CT	MBR 2050 CT	MBR 2060 CT	MBR 2090 CT	MBR 20100 CT	MBR 20150 CT	MBR 20200 CT	
Repetitive peak reverse voltage	V _{RRM}	35	45	50	60	90	100	150	200	V
Reverse voltage, total rms value	V _{R(RMS)}	24	31	35	42	63	70	105	140	V
Forward current	I _F		20						А	
Surge peak forward current, 8.3ms single half sine wave superimposed on rated load	I _{FSM}		150						A	
Peak repetitive reverse surge current ⁽¹⁾	I _{RRM}	1 0.5						А		
Peak repetitive forward current (Rated V _R , Square wave, 20KHz)	I _{FRM}		20					А		





MBR2035CT – MBR20200CT Taiwan Semiconductor

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)										
PARAMETER	SYMBOL	MBR 2035 CT	MBR 2045 CT	MBR 2050 CT	MBR 2060 CT	MBR 2090 CT	MBR 20100 CT	MBR 20150 CT	MBR 20200 CT	UNIT
Critical rate of rise of off- state voltage	dv/dt		10,000				V/µs			
Junction temperature	TJ		-55 to +150				°C			
Storage temperature	T _{STG}		-55 to +150			°C				

Notes:

1. tp = 2.0µs, 1.0KHz

THERMAL PERFORMANCE				
PARAMETER		SYMBOL	ТҮР	UNIT
Junction-to-case thermal resistance	MBR2035CT		1	
	MBR2045CT	Б		0000
	MBR2050CT	R _{eJC}		°C/W
	MBR2060CT			
	MBR2090CT		2	
Junction-to-case thermal resistance	MBR20100CT	Б		°C/W
	MBR20150CT	R _{eJC}		C/VV
	MBR20200CT			

PARAMETER		CONDITIONS	SYMBOL	ΤΥΡ	MAX	UNIT
	MBR2035CT MBR2045CT	I _F = 10A, T _J = 25°C		-	-	V
	MBR2050CT MBR2060CT			-	0.80	V
	MBR2090CT MBR20100CT			-	0.85	V
	MBR20150CT MBR20200CT		VF	-	0.99	V
	MBR2035CT MBR2045CT			-	0.84	V
Forward voltage per diode ⁽¹⁾	MBR2050CT MBR2060CT MBR2090CT MBR20100CT	I _F = 20A, T _J = 25°C		-	0.95	v
	MBR20150CT MBR20200CT			-	1.23	V
	MBR2035CT MBR2045CT			-	0.57	V
	MBR2050CT MBR2060CT			-	0.70	V
	MBR2090CT MBR20100CT	l _F = 10A, T _J = 125°C		-	0.75	V
	MBR20150CT MBR20200CT			-	0.87	V
	MBR2035CT MBR2045CT			-	0.72	V
	MBR2050CT MBR2060CT MBR2090CT MBR20100CT	I _F = 20A, T _J = 125°C		-	0.85	V
	MBR20150CT MBR20200CT			-	1.10	V



PARAMETER		CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Reverse current @ rated V _R	MBR2035CT MBR2045CT MBR2050CT MBR2060CT MBR2090CT MBR20100CT MBR20150CT MBR20200CT	T _J = 25°C		-	100	μΑ
per diode ⁽²⁾	MBR2035CT MBR2045CT	− T _J = 125°C	I _R	-	15	mA
	MBR2050CT MBR2060CT			-	10	mA
	MBR2090CT MBR20100CT MBR20150CT			-	5	mA
	MBR20200CT	1		-	0.15	mA

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION		
ORDERING CODE ⁽¹⁾⁽²⁾	PACKAGE	PACKING
MBR20xCT	TO-220AB	50 / Tube
MBR20xCTH	TO-220AB	50 / Tube

Notes:

1. "x" defines voltage from 35V(MBR2035CT) to 200V(MBR20200CT)

2. "H" means AEC-Q101 qualified



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

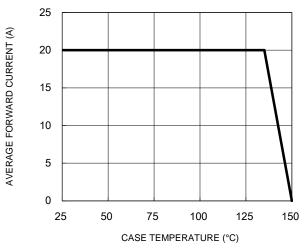


Fig.3 Typical Reverse Characteristics

Fig.1 Forward Current Derating Curve

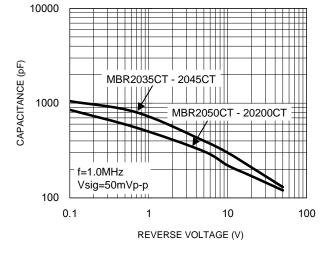
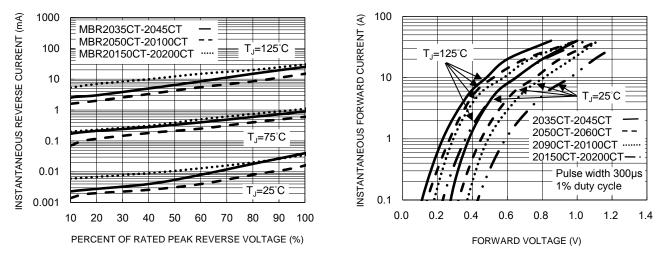


Fig.2 Typical Junction Capacitance

Fig.4 Typical Forward Characteristics



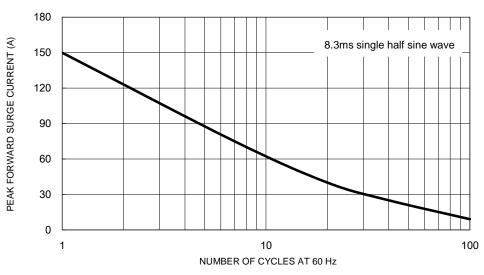


Fig.5 Maximum Non-Repetitive Forward Surge Current



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

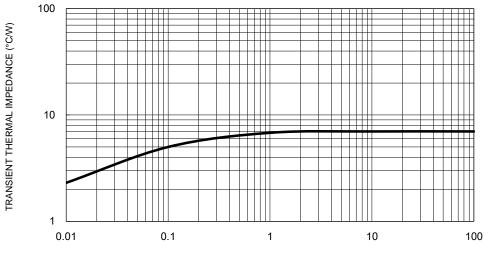


Fig.6 Typical Transient Thermal Impedance

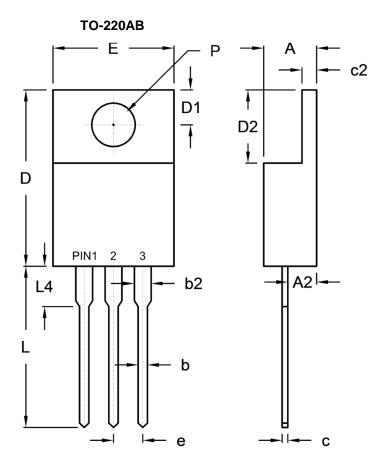
PULSE DURATION (s)



MBR2035CT - MBR20200CT

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PACKAGE OUTLINE DIMENSIONS



DIM.	Unit	(mm)	Unit ((inch)
	Min.	Max.	Min.	Max.
A	4.42	4.76	0.174	0.187
A2	2.20	2.80	0.087	0.110
b	0.68	0.94	0.027	0.037
b2	1.14	1.77	0.045	0.070
с	0.35	0.64	0.014	0.025
c2	1.14	1.40	0.045	0.055
D	14.60	16.00	0.575	0.630
D1	2.62	3.44	0.103	0.135
D2	5.84	6.86	0.230	0.270
E	-	10.50	-	0.413
е	2.41	2.67	0.095	0.105
L	13.19	14.79	0.519	0.582
L4	2.80	4.20	0.110	0.165
Р	3.54	4.00	0.139	0.157

MARKING DIAGRAM



P/N	= Marking Code
G	= Green Compound
YWW	= Date Code
F	= Factory Code



MBR2035CT - MBR20200CT

Taiwan Semiconductor

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